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SERIAL NUMBER 09/726,860	FILING DATE 11/30/2000 RULE	CLASS 117	GROUP ART UNIT 1765	ATTORNEY DOCKET NO. 09792909-4715	
<p>APPLICANTS</p> <p>Etsuo Morita, Kanagawa, JAPAN;</p> <p>** CONTINUING DATA ***** <i>MA 7/15/2002</i></p> <p>** FOREIGN APPLICATIONS ***** <i>MA 7/15/2002</i></p> <p>JAPAN P11-345246 12/03/1999</p> <p>IF REQUIRED, FOREIGN FILING LICENSE GRANTED</p> <p>** 01/22/2001</p>					
<p>Foreign Priority claimed <input checked="" type="checkbox"/> yes <input type="checkbox"/> no</p> <p>35 USC 119 (a-d) conditions <input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after Allowance</p> <p>met</p> <p>Verified and Acknowledged</p>		<p>STATE OR COUNTRY JAPAN</p>	<p>SHEETS DRAWING 10</p>	<p>TOTAL CLAIMS 30</p>	<p>INDEPENDENT CLAIMS 4</p>
<p>ADDRESS</p> <p>26263</p> <p>SONNENSCHN NATH & ROSENTHAL</p> <p>P.O. BOX 061080</p> <p>WACKER DRIVE STATION</p> <p>CHICAGO, IL</p> <p>60606-1080</p>					
<p>TITLE</p> <p>Method of manufacturing crystal of III-V compound of the nitride system, crystal substrate of III-V compound of the nitride system, crystal film of III-V compound of the nitride system, and method of manufacturing device</p>					
<p>FILING FEE</p> <p>RECEIVED</p> <p>1100</p>	<p>FEES: Authority has been given in Paper</p> <p>No. _____ to charge/credit DEPOSIT ACCOUNT</p> <p>No. _____ for following:</p>		<p><input type="checkbox"/> All Fees</p> <p><input type="checkbox"/> 1.16 Fees (Filing)</p> <p><input type="checkbox"/> 1.17 Fees (Processing Ext. of time)</p> <p><input type="checkbox"/> 1.18 Fees (Issue)</p> <p><input type="checkbox"/> Other _____</p> <p><input type="checkbox"/> Credit</p>		